



JOC305XM4 Series

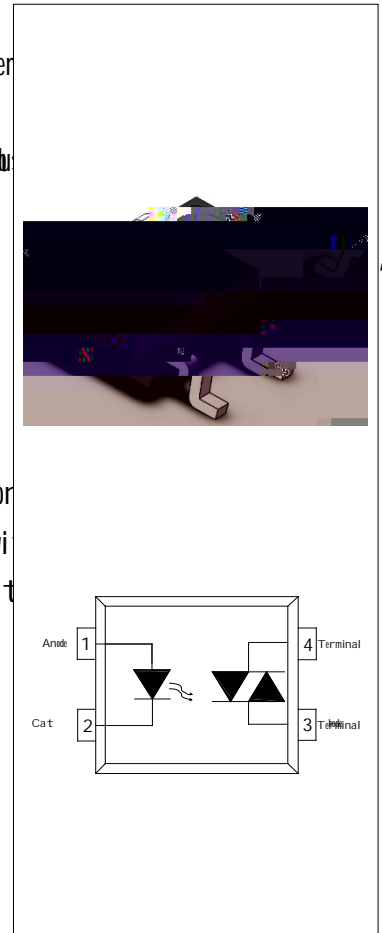
Rev.A.1.0

FEATURES

The JOC30 5XM4 series combine an Al GaAs infrared emit diode as t silicon random -phase phot SOP4 pack With t series provide t are widel ysed in sol enoid/val ue cont mot sol id st peripheral s.

PARAMETERS

High isol at 3750 VRMS
 DC input -phase phot
 Operat 55 to 100
 REACH & RoHS compl iance
 Hal ogen free
 MSL cl ass 1
 HBM : H3A ; MM: M4
 CQC approved
 VDE approved
 UL approved



ABSORPTION

(Temperat

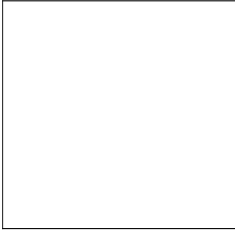
Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	60	mA
	Reverse Volt	V_R	6	age V
	Junct	T_j	125	ion Temperat
	Input	P_I	100	Power Dissipat
	Power Dissipat ($T_a = 25^\circ C$)	$P_D /$	-1.33	ion Derat mW /
Out	Offst Volt	V_{OFF}	600	age V
	Peak On-state Current (100µs pulse, 120 pps)	$I_{T(P)}$	2	A
	On-st	$I_{T(RMS)}$	100	at mA
	Peak Current ($w = 10$ ms)	I_{TSM}	1	(P A

Q

ADME

SD

MAED



CS

FIG.1: Forward Current

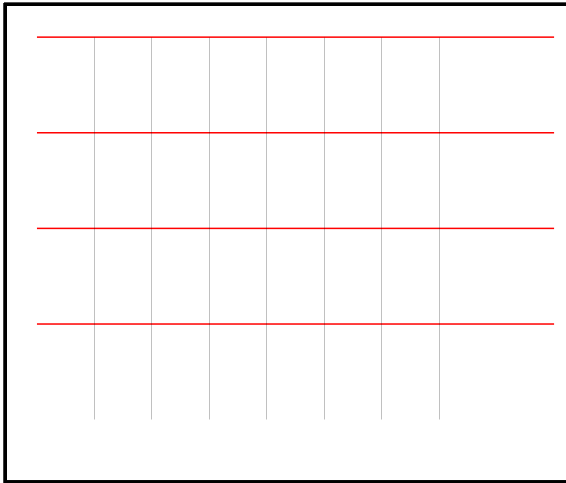


FIG.2: On-st vs. Ambient

Temperat 1000(mA) 200 -0.1m1 DoTI S Tw c..000202 C

TEST

FIG.12: Test

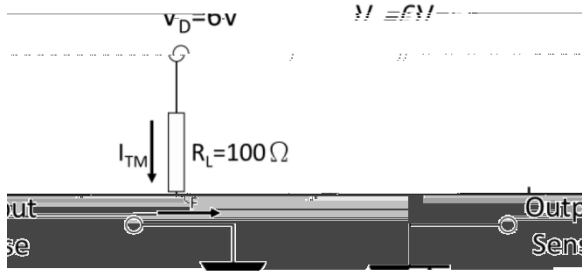


FIG.13: Waveforms of Turn On Time

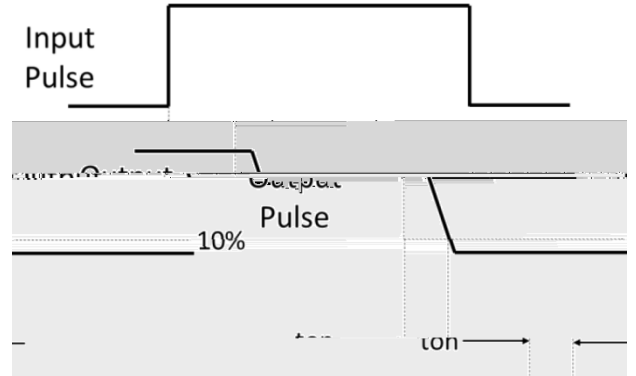


Fig.14: Test Circuits of dV/dt

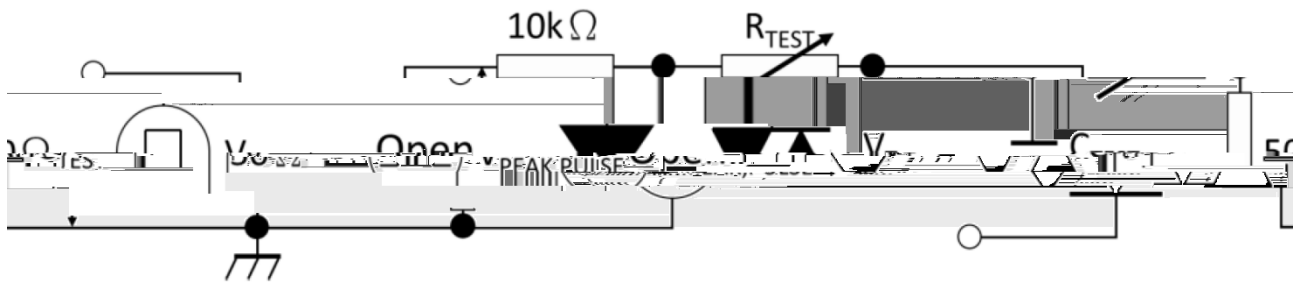
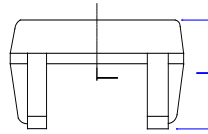
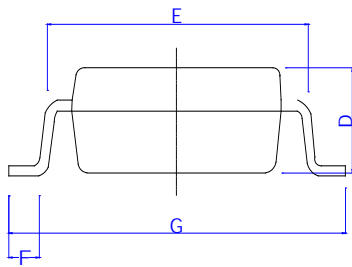
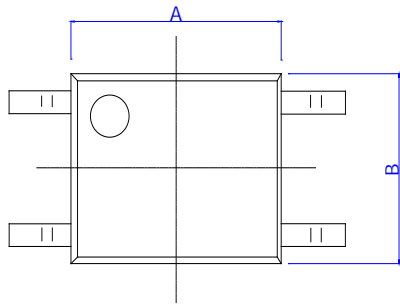


Fig.15: Waveforms of dV/dt





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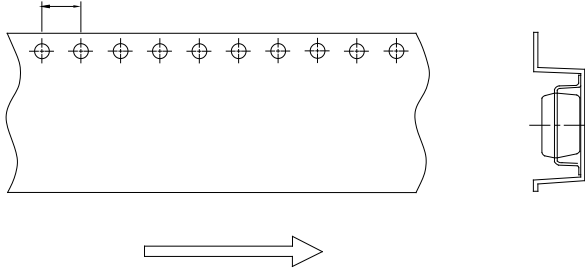
Ref.	Dimensions					
	Millimet			Inches		
	Min.	Typ.	Max	Min.	Typ.	Max
A	4.20		4.85	0.165		0.191
B	3.30		4.40	0.130		0.173
C						
D	1.75		2.80	0.069		0.110
E	4.90		5.80	0.193		0.228
F						
G	6.30			0.248		
H						
I						
J						

CAR BEAD



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R52C5

